

ABSTRACT OF THE DISCLOSURE

A semiconductor element is formed over a surface of a semiconductor substrate. A first insulating film is formed over the surface of the semiconductor substrate, the first insulating film covering the semiconductor
5 element. A second insulating film is formed over the first insulating film, the second insulating film having a dielectric constant lower than that of the first insulating film. A first wiring pattern is formed over the second insulating film. A conductive connection member buried in the second and first insulating films electrically interconnects the first wiring pattern and semiconductor element.